

DERWENT-ACC-NO: 2003-360704

DERWENT-WEEK: 200334

COPYRIGHT 2006 DERWENT INFORMATION LTD

TITLE: Method for activating dopants

INVENTOR: CHA, T H; LIM, G Y

PATENT-ASSIGNEE: HYNIX SEMICONDUCTOR INC [HYNIN]

PRIORITY-DATA: 2001KR-0038023 (June 29, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES	MAIN-IPC	
KR 2003002424 A	January 9, 2003	N/A
001	H01L 021/265	

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
KR2003002424A	N/A	2001KR-0038023
June 29, 2001		

INT-CL (IPC): H01L021/265

ABSTRACTED-PUB-NO: KR2003002424A

BASIC-ABSTRACT:

NOVELTY - A method for activating dopants is provided to easily control the temperature compared to the conventional RTA(Rapid Thermal Annealing) method by locally heating a silicon substrate by using a laser.

DETAILED DESCRIPTION - In order to activate a p-type or n-type dopants in a silicon substrate(10), an infrared laser(20) having a desired wavelength is irradiated into the silicon substrate(10). At this time, the wavelength of the infrared laser(20) is determined by a vibration mode of silicon. By analyzing infrared absorption spectrum, the vibration mode of silicon is calculated.

Preferably, the wavelength of the infrared laser(20) is 16-17 micrometer.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD ACTIVATE DOPE

DERWENT-CLASS: U11

EPI-CODES: U11-C03D;

